

**AMENDMENTS TO THE CLAIMS**

Please replace the claims, including all prior versions, with the listing of claims found below.

**Listing of Claims:**

1. (Original) A method for removing a resist from a liner on a mask on a semiconductor substrate, comprising:  
providing an etching plasma comprising at least hydrogen at a predetermined temperature level and a predetermined pressure level in a reaction chamber; and  
etching the resist selectively to the mask with the plasma for a predetermined period of time.
2. (Original) The method according to claim 1, wherein the etching plasma comprises of a predetermined amount of nitrogen as a diluent.
3. (Currently Amended) The method according to claim 2, wherein a ratio of ~~Nitrogen~~ nitrogen to ~~Hydrogen~~ hydrogen is varied starting from a standard ~~Nitrogen~~ nitrogen to ~~Hydrogen~~ hydrogen mixture of 96:4 to a stronger ~~Hydrogen~~ hydrogen rich chemistry based on an intended application.
4. (Currently Amended) The method according to claim 1, wherein the etching plasma ~~is~~ comprises ~~comprised~~ of a predetermined amount of CF<sub>4</sub>.
5. (Original) The method according to claim 4, wherein the predetermined amount is less than 5 per cent.
6. (Original) The method according to claim 1, wherein the etching plasma is free of oxygen.
7. (Original) The method according to claim 1, wherein the predetermined pressure level of the etching plasma is in the range of 50 to 300 Pa.

8. (Original) The method according to claim 1, wherein the predetermined temperature is in the range of 150°C to 350°C.

9. (Currently Amended) The method according to claim 1, wherein ~~the~~ a lithography mask consists of a hard mask.

10. (Currently Amended) The method according to claim 9, wherein ~~the~~ a hard mask consists of carbon.

11. (Original) The method according to claim 1, wherein the resist is a carbon-based photo resist.

12. (Currently Amended) The method according to claim 1, wherein ~~the~~ a liner comprising of SiON is deposited on the mask prior to depositing and stripping the resist.

13. (Original) The method according to claim 1, wherein the semiconductor substrate is a Si-substrate.

14. (Currently Amended) The method according to claim 1, wherein the resist has a selectivity ~~of to the mask to the resist~~ is equal or higher than 10, ~~preferably higher than 15~~.

15. (Original) The method according to claim 1, wherein the resist is stripped with an across wafer non-uniformity of <3% one sigma.

16. (Original) The method according to claim 1, wherein the resist mask is stripped completely from the surface of the semiconductor substrate.